

LED780-PD010-40D52

LED780-PD010-40D52 consists of a GaAlAs LED 780 nm and a Si-PD mounted onTO-18 stem hermetically sealed with a glass flat can, and is designed to monitor reflected light through detector for controlling its own output power.

Specifications

Product Name: LED Lamp with PD Monitor Type No.: LED780-PD010-40D52 Chip material: GaAlAs , Si (PIN) Peak wavelength: 780 nm Package: Stem TO-18 Lens: Ø5 2.4 Flat Glass Can: Metal Can (Gold Plate)





Unit: mm

v 1.1 19.09.2014

Absolute Maximum Ratings [Ta=25°C]

Device	Item	Symbol	Maximum Rated	Unit
LED	Power Dissipation	P _D	200	mW
LED	Forward Current	I _F	100	mA
LED	Pulse Forward Current	I _{FP}	500	А
LED	Reverse Voltage	V _R	5	V
PD	Reverse Voltage	V _R	100	V
	Operating Temperature	T _{CASE}	-20 ~ +85	°C
	Storage Temperature	T _{STG}	-30 ~ +100	°C
	Soldering Temperature	T _{SLD}	260	°C

Pulse Forward Current condition: Duty = 1%, tw = 10 μ s

Soldering condition: Soldering condition must be completed within 3 seconds at 250°C

Electro-Optical Charactaristics [Ta=25°C]

Item	Symbol	Condition	Min.	Тур.	Max.	Unit
Forward Voltage	V _F	IF=50mA		1.70	2.00	V
Reverse Current	I_R	VR=5V			10	uA
Total Radiated Power	Po	IF=50mA	3.0	6.0		mW
Radiant Intensity	IE	IF=50mA	2.5	5.0		mW/sr
Peak Wavelength	λ_P	IF=50mA	765	780	795	nm
Half Width	$\Delta \lambda$	IF=50mA		35		nm
Viewing Half Angle	arphi	IF=50mA		±55		deg.
Rise Time	t _R	IF=50mA		60		ns
Fall Time	t _F	IF=50mA		40		ns
Output Current	IL	VR=0V	250	500		uA
Dark Current	ID	VR=10V			10	nA

Total Radiated Power is measured by Photodyne #500

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